

ABSTRACT OF THE DISCLOSURE

Low dielectric materials and films comprising same have been identified for
5 improved performance when used as interlevel dielectrics in integrated circuits as well as
methods for making same. In certain embodiments of the invention, there is provided a
low-temperature process to remove at least a portion of at least one pore-forming
material within a composite film thereby forming a porous film. The pore-forming
material may be removed via exposure to at least one energy source, preferably an
10 ultraviolet light source, in a non-oxidizing atmosphere.

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